

# Improvement of the thermoelectric performance of boron-doped silicon by blocking minority carrier diffusion on the p<sup>+</sup>/p interface

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## Notice of Corrections

The place is indicated by page (p.), line (l.), and other directives as relevant. Original text follows the word “for” and the corrected text follows “read.” Original and corrected text passages are given within quotation marks.

p. 2, l. 9: for “Bi-Te <sup>2)</sup> and Pb-Te <sup>3)</sup>” read “Bi-Te <sup>2,3)</sup> and Pb-Te <sup>4)</sup>”

p. 3, l. 31: for “9 g” read “1.8 g”

p. 4, l. 7: for “18 g” read “3.6 g”

p. 4, l. 8: for “18 g” read “3.6 g”

p. 4, l. 21: for “0.25 mm” read “250  $\mu\text{m}$ ”

p. 5, l. 17–18: for “p-p<sup>+</sup>-Si,” read “p<sup>+</sup>-Si,”

p. 6, l. 21: for “line (e),” read “line (e) at temperature above 325 K,”

p. 7, l. 18: for “minor” read “minority”

Fig. 2: for “202” read “220”